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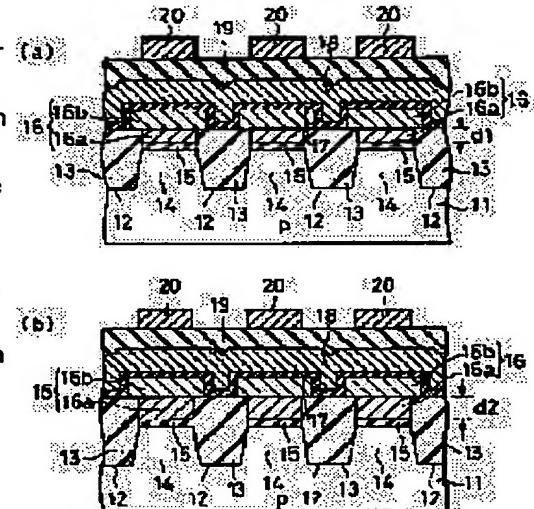
(71)Applicant : TOSHIBA CORP
 (72)Inventor : NARITA KAZUHITO
 SHIMIZU KAZUHIRO
 WATANABE TOSHIHARU
 ARITOME SEIICHI

(54) NONVOLATILE SEMICONDUCTOR STORAGE DEVICE AND MANUFACTURE THEREOF

(57)Abstract:

PROBLEM TO BE SOLVED: To provide an EEPROM, in which coupling capacity between a floating gate and a control gate is increased, and the dispersion of memory-cell characteristics based on in-plane dispersion in the etch-back process of an element-isolation insulating film can be reduced.

SOLUTION: A tunnel oxide film 15 and a first conductive layer 16a are laminated on a substrate 11, a mask material for partitioning an element region 14 is formed onto the first conductive layer 16a in a pattern, the first conductive layer 16a and the tunnel oxide film 15 are etched successively, and the substrate 11 is etched to a specified depth to form grooves 12. Element-isolation insulating films 13 are deposited, while leaving the mask material, the insulating films 13 are CMP-polished so that the mask material under insulating films 13 is removed completely and the face of the first conductive layer 16a is exposed being flush with the plane of the insulating films 13, second conductive layers 16b constituting floating gates 16 together with first conductive layers 16b are deposited on the first conductive layer 16a and the insulating films 13, slits for isolation are worked on the second conductive layers 16b for isolation, and a control gate 18 is formed via an ONO film 17.



LEGAL STATUS

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